

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-8 (Canceled).

Claim 9 (Currently Amended): A method according to claim [[8]] 16, wherein the ion implantation includes implanting ions chosen from among the following species: hydrogen and rare gases.

Claim 10 (Currently Amended): A method according to claim [[8]] 16, wherein the fastening includes a bonding chosen from bonding by molecular adhesion via intermediate films or without intermediate films, bonding by reaction, metallic bonding, brazing or bonding by species diffusion.

Claim 11 (Currently Amended): A method according to claim [[8]] 16, further comprising healing annealing of the implantation defects on the thin film.

Claim 12 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out before the thinning down the thin film.

Claim 13 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out after the thinning down the thin film.

Claim 14 (Currently Amended): Application of the method according to claim [[8]] 16 to obtain a thin film of SiC, GaAs, GaN, diamond, or InP on a target substrate.

Claim 15 (Previously Presented): The application of Claim 14 to obtain a thin film of SiC of a thickness less than or equal to $0.5\text{ }\mu\text{m}$ and with a concentration of defects less than $9\cdot 10^{20}\text{ atoms/cm}^3$.

Claim 16 (New): A method for transferring an electrically active thin film of a given thickness from an initial substrate to a target substrate, including an ion implantation step through an implanted face of the initial substrate to create a buried, embrittled film at a determined depth in relation to the implanted face of the initial substrate, a thin film thus being delimited between the implanted face and the buried film, the method comprising the following successive steps:

- determining a profile of acceptor defects that will be created by the implantation step in the thin film from the implanted face towards the buried film, said profile allowing to obtain said electrically active thin film of a given thickness wherein a number of acceptor defects is compatible with predetermined electrical properties of the thin film;

- carrying on said implantation step of the profile that was determined in said determining step;

- fastening the implanted face of the initial substrate with a face of the target substrate;

- separating the thin film from a remainder of the initial substrate at a level of the buried film; and

- thinning down the thin film transferred on the target substrate until the given thickness is reached.